



# 100V 1.3mΩ TOLL N-Ch Power MOSFET

## Features

- Ultra-low  $R_{DS(ON)}$
- Low Gate Charge
- 100% UIS Tested, 100%  $R_g$  Tested
- Pb-free Lead Plating
- Halogen-free and RoHS-compliant

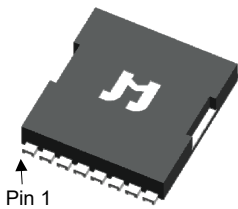
## Product Summary

Parameter	Value	Unit
$V_{DS}$	100	V
$V_{GS(th\_Typ)}$	2.8	V
$I_D (@ V_{GS} = 10V)^{(1)}$	411	A
$R_{DS(ON\_Typ)} (@ V_{GS} = 10V)$	1.3	mΩ

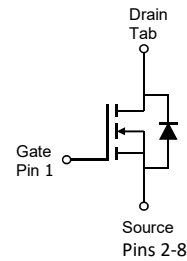
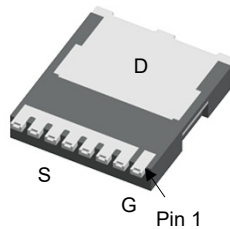
## Applications

- Power Management in Telecom., Industrial Automation, CE
- Current/Voltage Switching in DC/DC & AC/DC Sub-systems
- Motor Driving or BMS in Power Tool, E-vehicle, Robotics

PowerJE®10x12 Top View



PowerJE®10x12 Bottom



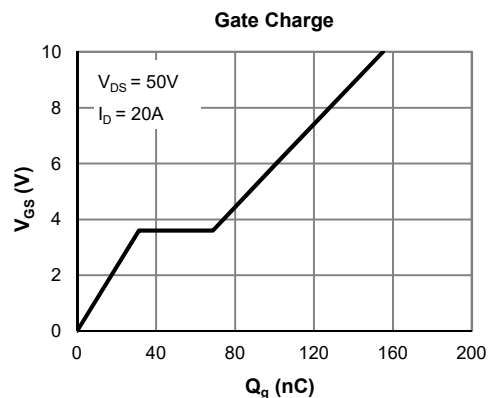
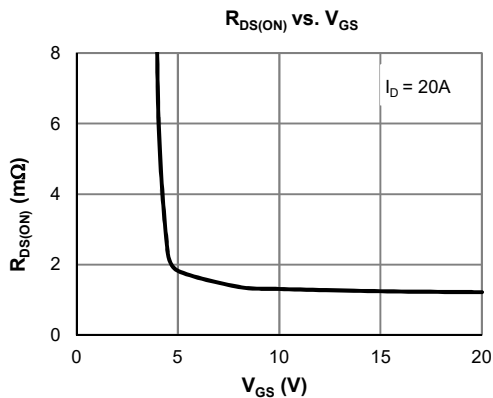
## Ordering Information

Device	Package	# of Pins	Marking	MSL	$T_J$ (°C)	Media	Quantity (pcs)
JMSH1001ATL-13	PowerJE®10x12 <sup>(1)</sup>	8	SH1001A	1	-55 to 175	13-inch Reel	2000

Note 1: PowerJE® is a registered trademark of JieJie Micro., its package outline is compatible to that of TO-LeadLess (TOLL).

## Absolute Maximum Ratings (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	$V_{DS}$	100	V
Gate-to-Source Voltage	$V_{GS}$	±20	V
Continuous Drain Current <sup>(2)</sup>	$I_D$	$T_C = 25^\circ\text{C}$	411
		$T_C = 100^\circ\text{C}$	290
Pulsed Drain Current <sup>(3)</sup>	$I_{DM}$	1343	A
Avalanche Current <sup>(4)</sup>	$I_{AS}$	50	A
Avalanche Energy <sup>(4)</sup>	$E_{AS}$	1250	mJ
Power Dissipation <sup>(5)</sup>	$P_D$	$T_C = 25^\circ\text{C}$	500
		$T_C = 100^\circ\text{C}$	250
Junction & Storage Temperature Range	$T_J, T_{STG}$	-55 to 175	°C



**Electrical Characteristics** (@  $T_J = 25^\circ\text{C}$  unless otherwise specified)

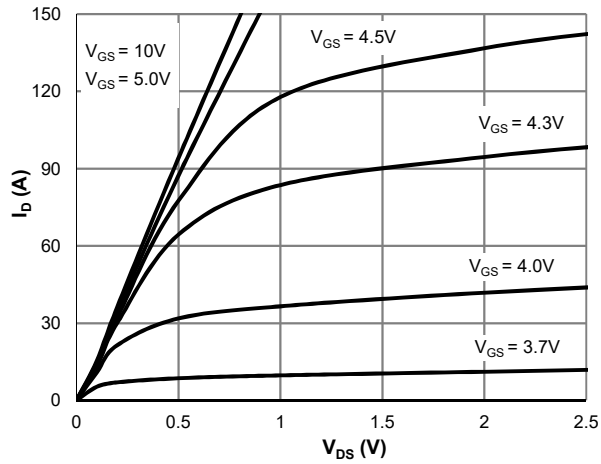
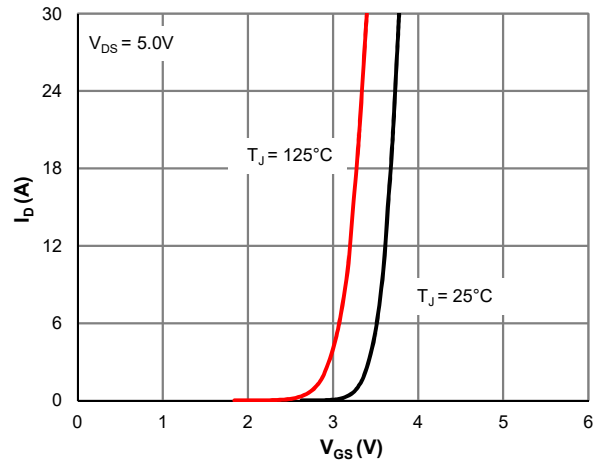
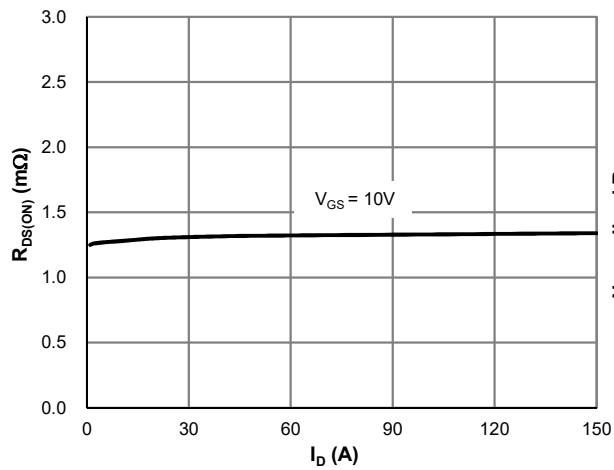
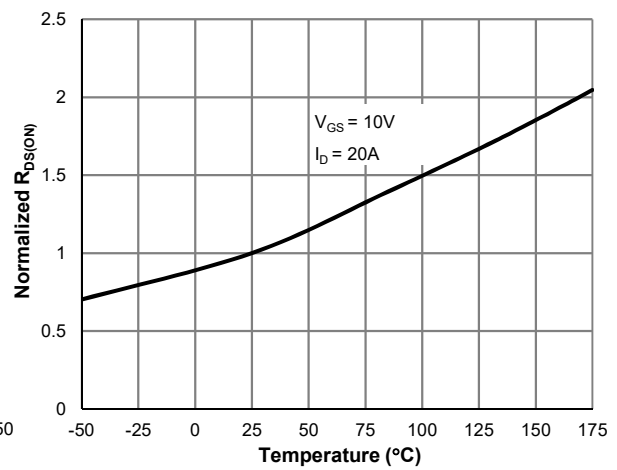
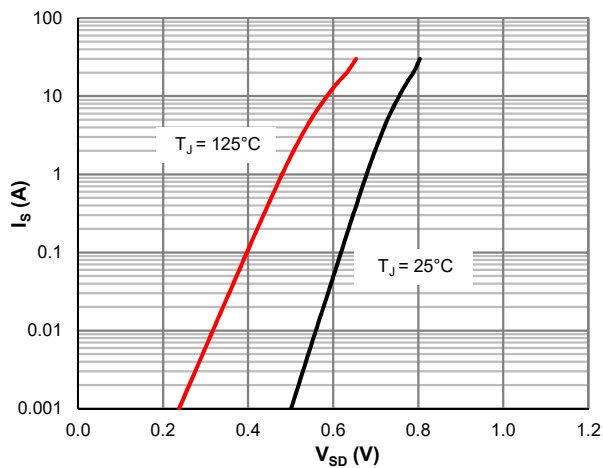
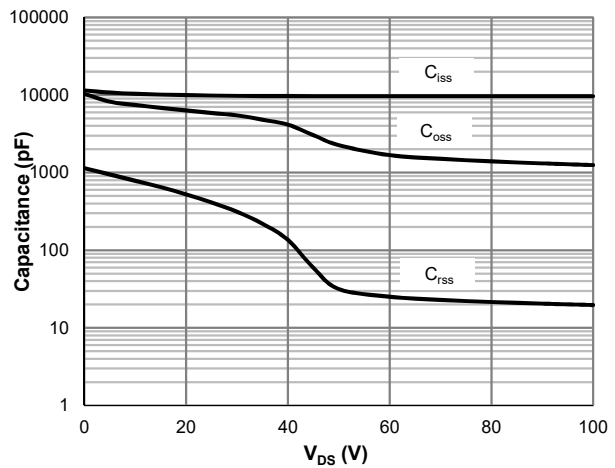
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit	
<b>STATIC PARAMETERS</b>							
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = 250\mu\text{A}, V_{GS} = 0\text{V}$	100			V	
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 80\text{V}, V_{GS} = 0\text{V}$			1.0	$\mu\text{A}$	
			$T_J = 55^\circ\text{C}$		5.0		
Gate-Body Leakage Current	$I_{GSS}$	$V_{DS} = 0\text{V}, V_{GS} = \pm 20\text{V}$			$\pm 100$	nA	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	2.0	2.8	4.0	V	
Static Drain-Source ON-Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{V}, I_D = 20\text{A}$		1.3	1.6	m $\Omega$	
Forward Transconductance	$g_{FS}$	$V_{DS} = 5\text{V}, I_D = 20\text{A}$		94		S	
Diode Forward Voltage	$V_{SD}$	$I_S = 1\text{A}, V_{GS} = 0\text{V}$		0.7	1.0	V	
Diode Continuous Current	$I_S$	$T_C = 25^\circ\text{C}$			500	A	
<b>DYNAMIC PARAMETERS</b> <sup>(6)</sup>							
Input Capacitance	$C_{iss}$	$V_{GS} = 0\text{V}, V_{DS} = 50\text{V}, f = 1\text{MHz}$		9623		pF	
Output Capacitance	$C_{oss}$				2091		pF
Reverse Transfer Capacitance	$C_{rss}$				32		pF
Gate Resistance	$R_g$	$V_{GS} = 0\text{V}, V_{DS} = 0\text{V}, f = 1\text{MHz}$		2.4		$\Omega$	
<b>SWITCHING PARAMETERS</b> <sup>(6)</sup>							
Total Gate Charge (@ $V_{GS} = 10\text{V}$ )	$Q_g$	$V_{GS} = 0 \text{ to } 10\text{V}$ $V_{DS} = 50\text{V}, I_D = 20\text{A}$		155		nC	
Total Gate Charge (@ $V_{GS} = 6.0\text{V}$ )	$Q_g$				101		nC
Gate Source Charge	$Q_{gs}$				31		nC
Gate Drain Charge	$Q_{gd}$				37		nC
Turn-On Delay Time	$t_{D(on)}$	$V_{GS} = 10\text{V}, V_{DS} = 50\text{V}$ $R_L = 2.5\Omega, R_{GEN} = 6\Omega$		34		ns	
Turn-On Rise Time	$t_r$				67		ns
Turn-Off Delay Time	$t_{D(off)}$				145		ns
Turn-Off Fall Time	$t_f$				111		ns
Body Diode Reverse Recovery Time	$t_{rr}$		$I_F = 15\text{A}, dI_F/dt = 100\text{A}/\mu\text{s}$		76		ns
Body Diode Reverse Recovery Charge	$Q_{rr}$	$I_F = 15\text{A}, dI_F/dt = 100\text{A}/\mu\text{s}$		116		nC	

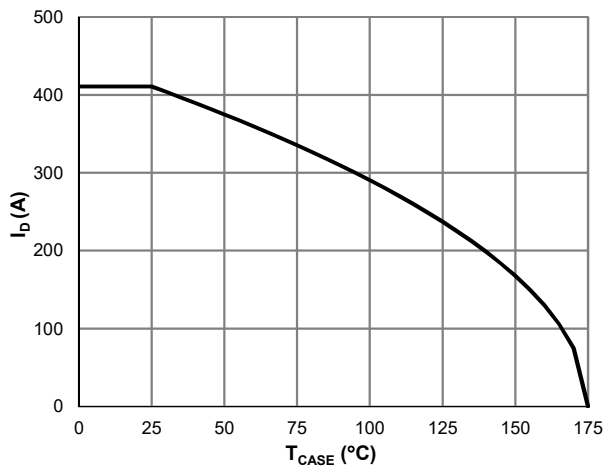
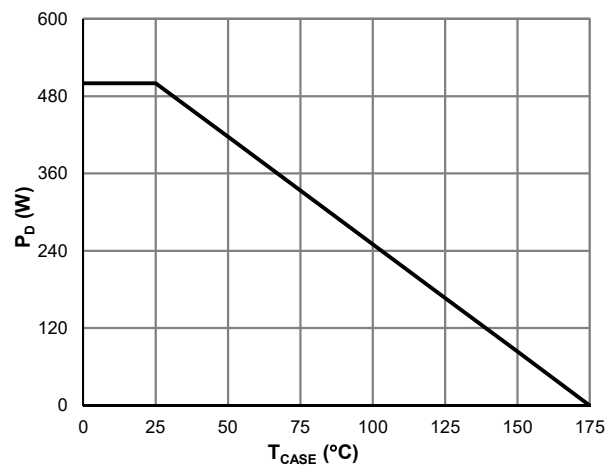
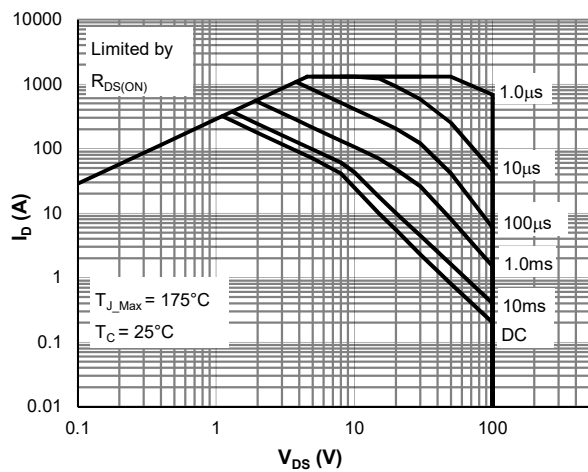
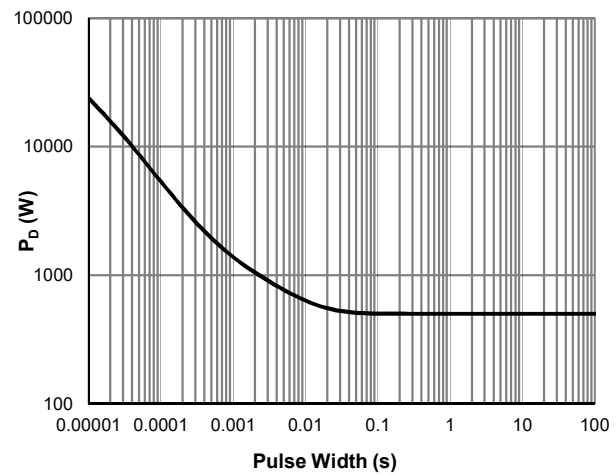
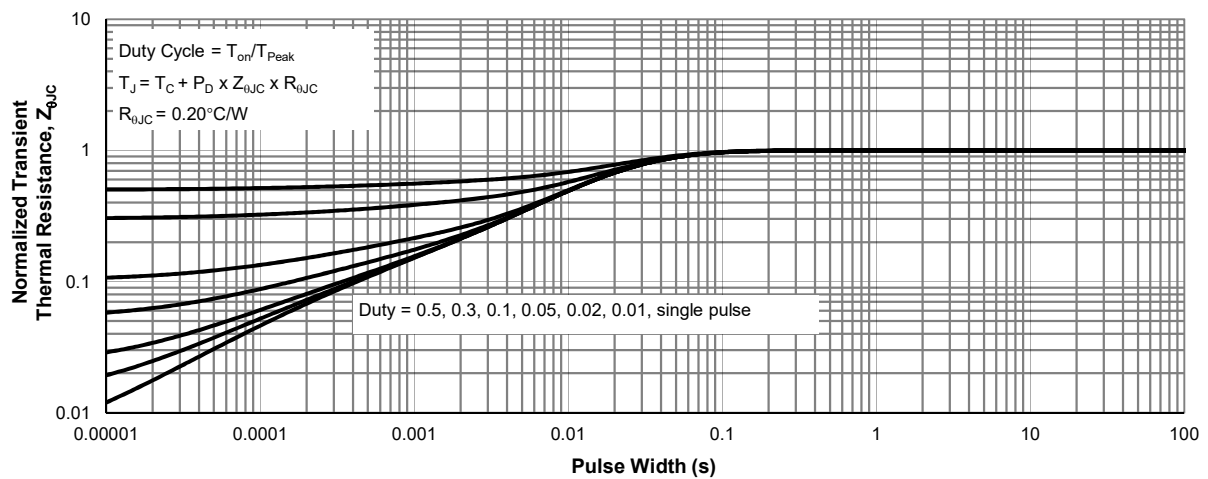
**Thermal Performance**

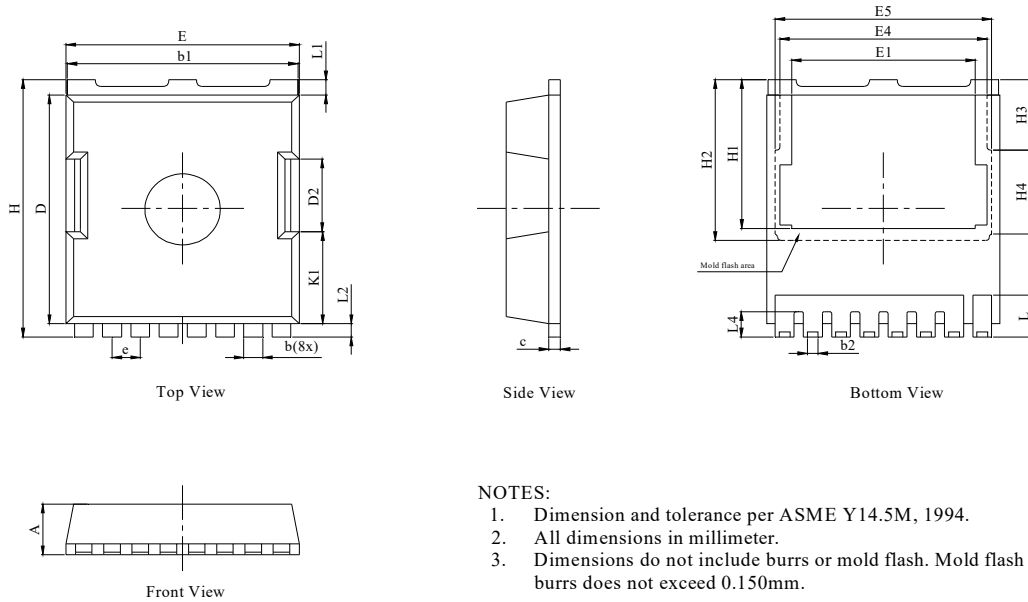
Parameter	Symbol	Typ.	Max.	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	35	45	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.20	0.30	$^\circ\text{C}/\text{W}$

**Notes:**

2. Computed continuous current assumes the condition of  $T_{J\_Max}$  while the actual continuous current depends on the thermal & electro-mechanical application board design.
3. This single-pulse measurement was taken under  $T_{J\_Max} = 175^\circ\text{C}$ .
4. This single-pulse measurement was taken under the following condition [ $L = 1\text{mH}, V_{GS} = 10\text{V}, V_{DD} = 50\text{V}$ ] while its value is limited by  $T_{J\_Max} = 175^\circ\text{C}$ .
5. The power dissipation  $P_D$  is based on  $T_{J\_Max} = 175^\circ\text{C}$ .
6. This value is guaranteed by design hence it is not included in the production test.

**Typical Electrical & Thermal Characteristics**

**Figure 1: Saturation Characteristics**

**Figure 2: Transfer Characteristics**

**Figure 3:  $R_{DS(ON)}$  vs. Drain Current**

**Figure 4:  $R_{DS(ON)}$  vs. Junction Temperature**

**Figure 5: Body-Diode Characteristics**

**Figure 6: Capacitance Characteristics**

**Typical Electrical & Thermal Characteristics**

**Figure 7: Current De-rating**

**Figure 8: Power De-rating**

**Figure 9: Maximum Safe Operating Area**

**Figure 10: Single Pulse Power Rating, Junction-to-Case**

**Figure 11: Normalized Maximum Transient Thermal Impedance**

**PowerJE<sup>®</sup> 10x12 Package Information**
**Package Outlines**

**NOTES:**

1. Dimension and tolerance per ASME Y14.5M, 1994.
2. All dimensions in millimeter.
3. Dimensions do not include burrs or mold flash. Mold flash or burrs does not exceed 0.150mm.

DIM.	MILLIMETER		
	MIN.	NOM.	MAX.
A	2.20	2.30	2.40
b	0.70	0.80	0.90
b1	9.70	9.80	9.90
b2	0.42	0.46	0.50
c	0.40	0.50	0.60
D	10.28	10.38	10.58
D2		3.30	
E	9.70	9.90	10.10
E1		7.80	
E4		8.80	
E5		9.20	
e	1.20 (BSC)		
H	11.48	11.68	11.88
H1	6.55	6.75	6.85
H2		7.30	
H3		3.20	
H4		3.80	
K1		4.18	
L	1.70	1.90	2.10
L1		0.70	
L2		0.60	
L4	1.00	1.15	1.30

**Recommended Soldering Footprint**
